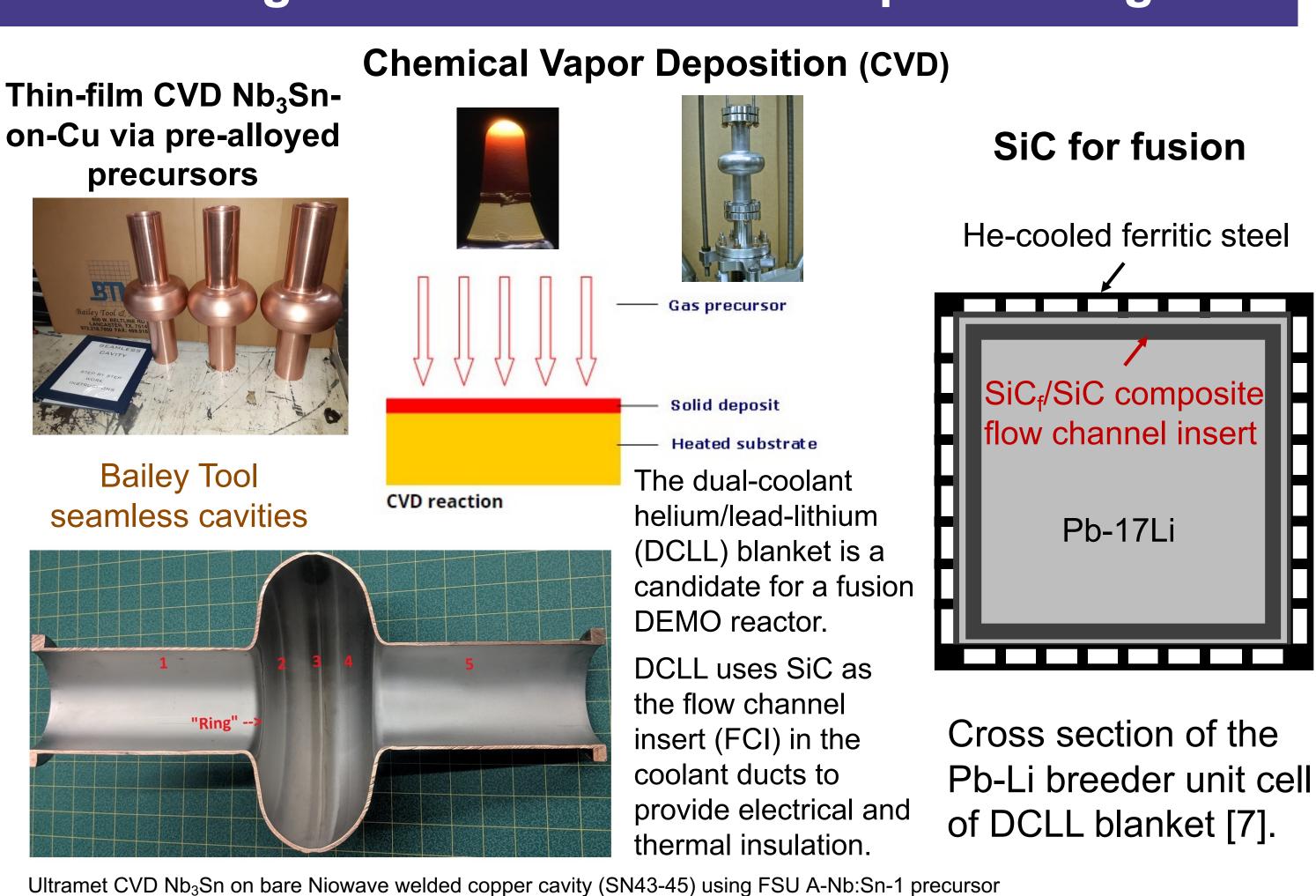
Machine learning enhanced microscopy identification of defects

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Why Machine Learning?

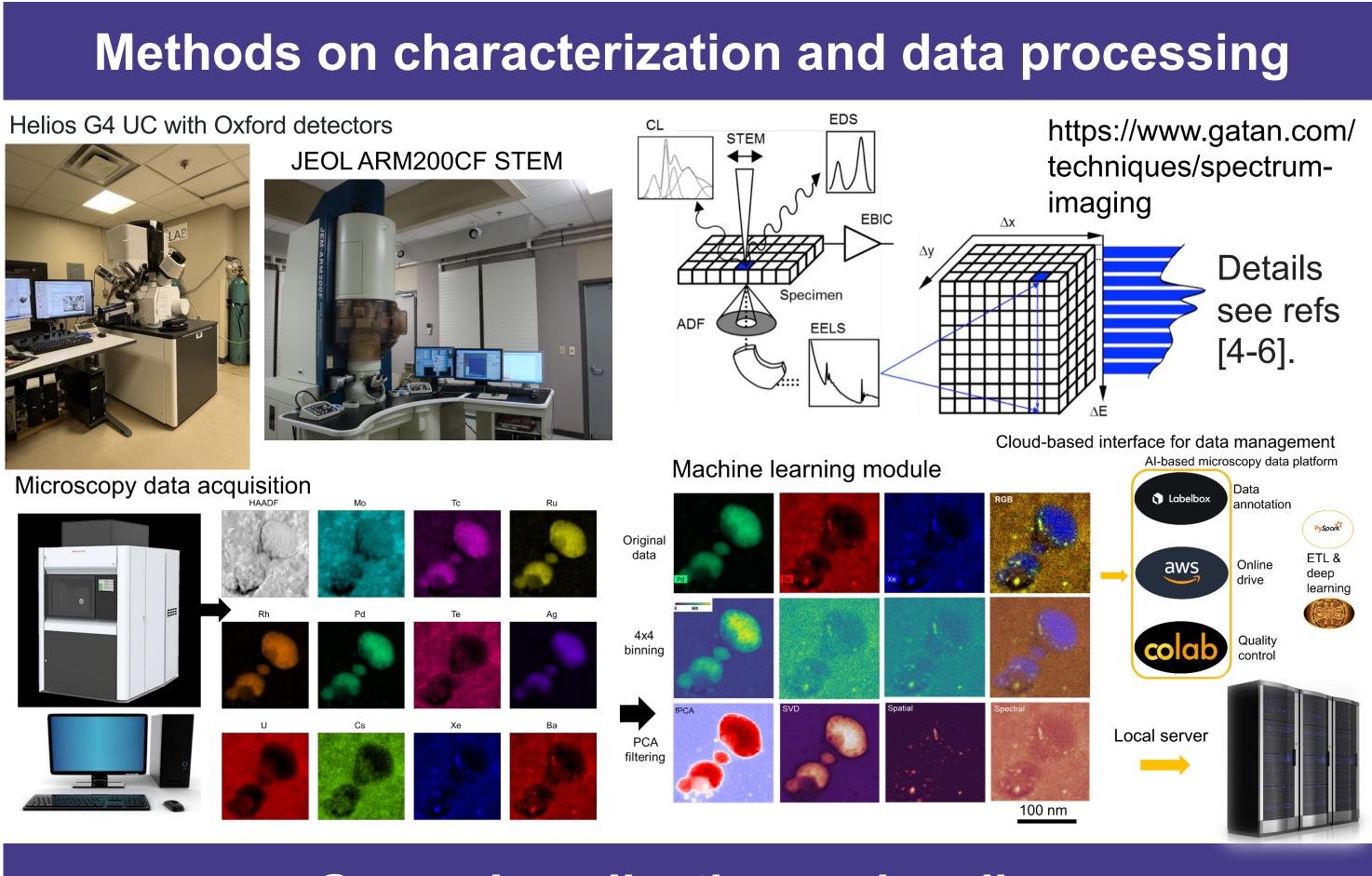
- This study focuses on the identification of defects in compounds for extreme applications: Nb₃Sn used in superconducting radio frequency cavities and SiC for fusion reactors.
- Machine learning algorithms have been applied to process atomistic structure images of interfaces of Cu/Nb₃Sn and defect evolution with an increase in irradiation dose in SiC.
- Advanced technology has facilitated the emergence of cuttingedge medical technologies, such as compact superconducting cyclotrons for external beam therapy with protons and ions.
- Thermo Fisher Scientific Talos F200X FEG-STEM and JEOL ARM200CF S/TEM were used for analytical microscopy for chemical composition using scanning transmission electron microscopy-energy dispersive X-ray spectroscopy (STEM-EDS) [1,2]. The process culminated with taking images of SiC defects that were analyzed through unsupervised machine learning algorithms.
- The results from the analysis provide insights into defect behavior to create strategies for maximizing the life and strength of materials[1,3]. The broader impact of this work would also result in cost and size reduction advantages in isotope production.
- We found defects with better resolution and confidence in the microstructure of these materials for extreme conditions.



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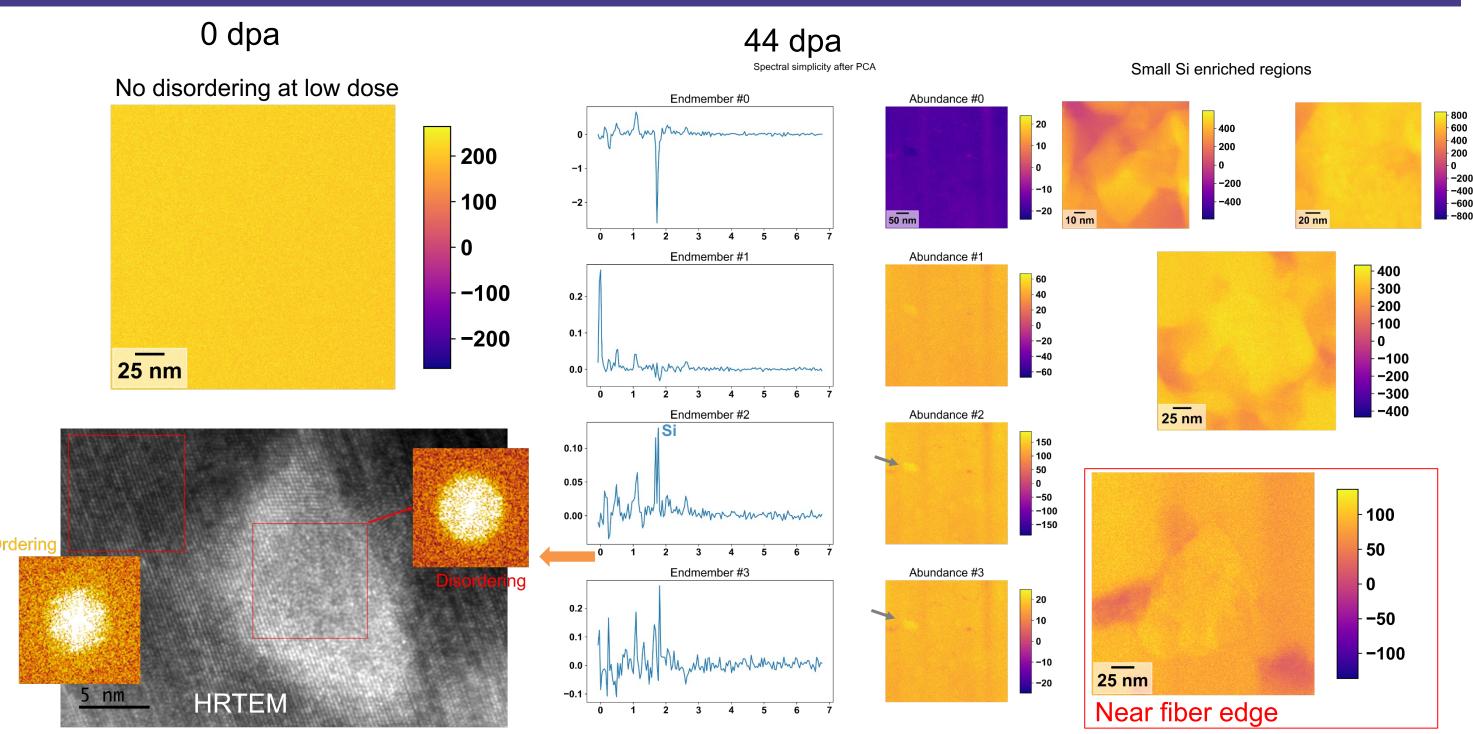
Background on materials and processing



General application and coding

- SiC is a wide gap semiconductor with decent radiation tolerance leads it to serve in extreme environments (space exploration, fusion reactors).
- The microstructural evolution of SiC under these conditions needs to be examined with modern electron microscopy.
- Establishing a machine learning (ML) platform using existing Python-based data science/ML libraries and data visualization tools to exhibit the defect evolution of SiC composite fiber with the increase of irradiation dose.
- An ML-enhanced approach helps better understand the defect behavior and proposes mitigation strategies to reduce their negative implications on structural materials.

Si Map in the irradiated SiC using Machine Learning

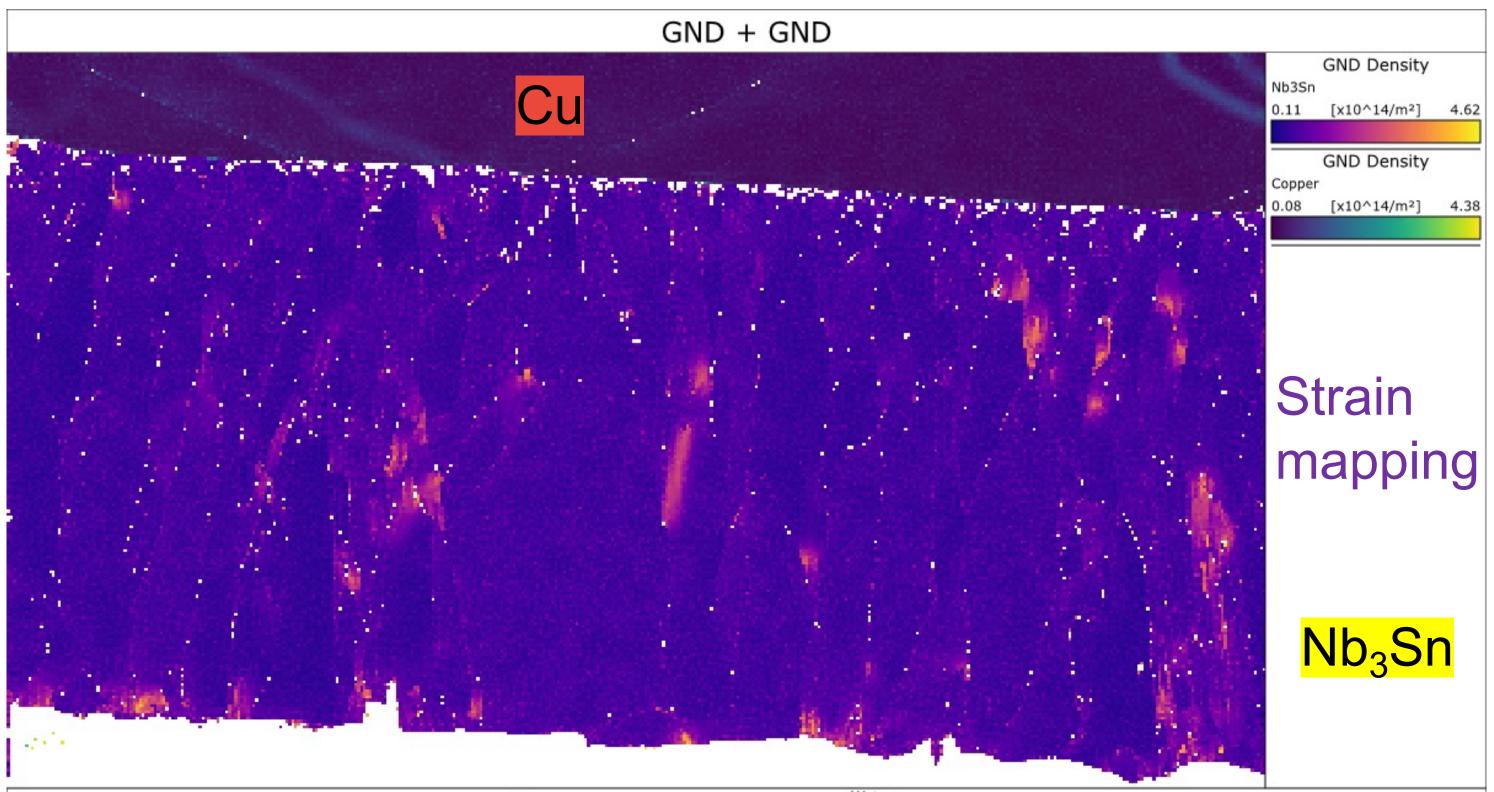


STEM-EDS maps on Si inside random single grains denoised the artifacts and low-counting background signals.

SCAN ME

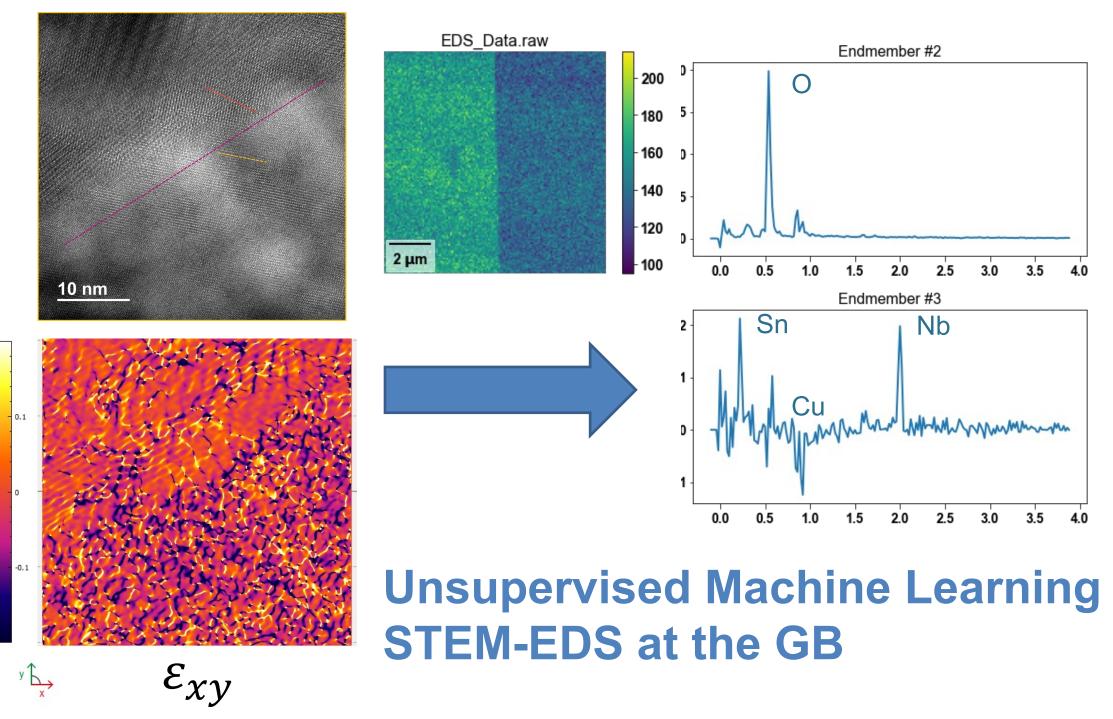






50µm

Looking at the Nb₃Sn Grain Boundary



- enhanced by machine learning.

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MAGNETIC FIELD LABORATORY

Thin-film Nb₃Sn-on-Cu ILC cavities interface

Raster: 421x242 Step Size: 0.3µm

Abundance #2

Cu segregation at the GB

Summary

The defect evolution was experimentally investigated through the construction of atomistic-level microscopy characterization

We found a detailed analysis of cavities and elemental distribution that is helpful to understand the effects of radiation of SiC and heterogeneity in Nb₃Sn thin films.

References







